

## Small Signal Schottky Diodes, Single & Dual

### Features

- These diodes feature very low turn-on voltage and fast switching.
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.

### Mechanical Data

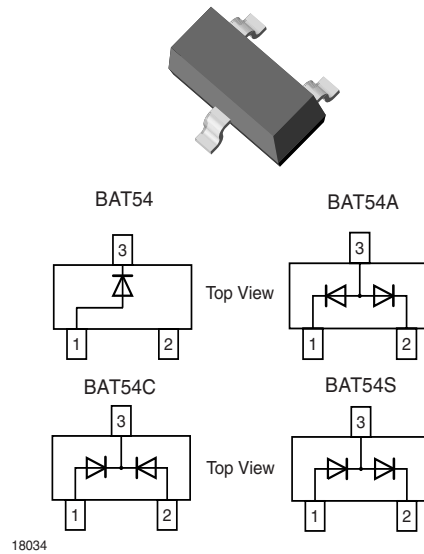
**Case:** SOT-23 Plastic case

**Weight:** approx. 8.8 mg

**Packaging Codes/Options:**

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box

GS08 / 3 k per 7" reel (8 mm tape), 15 k/box



### Parts Table

Part	Ordering code	Marking	Remarks
BAT54	BAT54-GS18 or BAT54-GS08	L4	Tape and Reel
BAT54A	BAT54A-GS18 or BAT54A-GS08	L42	Tape and Reel
BAT54C	BAT54C-GS18 or BAT54C-GS08	L43	Tape and Reel
BAT54S	BAT54S-GS18 or BAT54S-GS08	L44	Tape and Reel

### Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		$V_{RRM}$	30	V
Forward continuous current		$I_F$	200 <sup>1)</sup>	mA
Repetitive peak forward current		$I_{FRM}$	300 <sup>1)</sup>	mA
Surge forward current current	$t_p < 1\text{ s}$	$I_{FSM}$	600 <sup>1)</sup>	mA
Power dissipation		$P_{tot}$	230	mW

<sup>1)</sup> Device on fiberglass substrate, see layout on next page.

# BAT54 / 54A / 54C / 54S

Vishay Semiconductors

## Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		$R_{thJA}$	430 <sup>1)</sup>	$^{\circ}\text{C}/\text{W}$
Junction temperature		$T_j = T_{stg}$	- 65 to + 150	$^{\circ}\text{C}$
Storage temperature range		$T_S$	- 65 to + 150	$^{\circ}\text{C}$

<sup>1)</sup> Device on fiberglass substrate, see layout on next page.

## Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

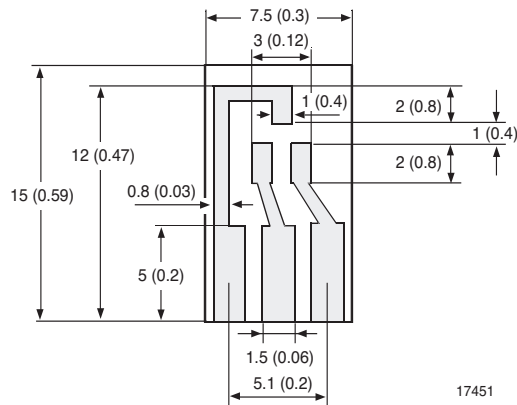
Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Reverse Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$ pulses	$V_{(BR)}$	30			V
Leakage current	Pulse test $t_p < 300\text{ }\mu\text{s}$ , $\delta < 2\%$ at $V_R = 25\text{ V}$	$I_R$			2	$\mu\text{A}$
Forward voltage	$I_F = 0.1\text{ mA}$ , $t_p < 300\text{ }\mu\text{s}$ , $\delta < 2\%$	$V_F$			240	mV
	$I_F = 1\text{ mA}$ , $t_p < 300\text{ }\mu\text{s}$ , $\delta < 2\%$	$V_F$			320	mV
	$I_F = 10\text{ mA}$ , $t_p < 300\text{ }\mu\text{s}$ , $\delta < 2\%$	$V_F$			400	mV
	$I_F = 30\text{ mA}$ , $t_p < 300\text{ }\mu\text{s}$ , $\delta < 2\%$	$V_F$			500	mV
	$I_F = 100\text{ mA}$ , $t_p < 300\text{ }\mu\text{s}$ , $\delta < 2\%$	$V_F$			1000	mV
Diode capacitance	$V_R = 1\text{ V}$ , $f = 1\text{ MHz}$	$C_{tot}$			10	pF
Reverse recovery time	$I_F = 10\text{ mA}$ through $I_R = 10\text{ mA}$ to $I_{rr} = 1\text{ mA}$ , $R_L = 100\text{ }\Omega$	$t_{rr}$			5	ns

## Layout for $R_{thJA}$ test

Thickness:

Fiberglass 1.5 mm (0.059 in.)

Copper leads 0.3 mm (0.012 in.)



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## Typical Characteristics ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

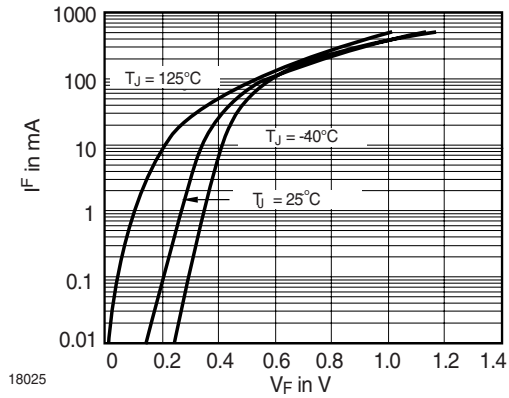


Figure 1. Typical Forward Voltage Forward Current at Various Temperatures

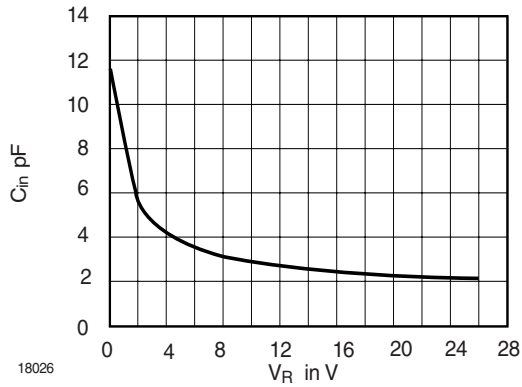


Figure 2. Typical Capacitance  $^{\circ}\text{C}$  vs. Reverse Applied Voltage  $V_R$

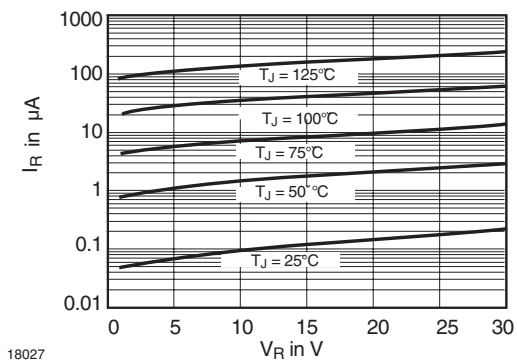
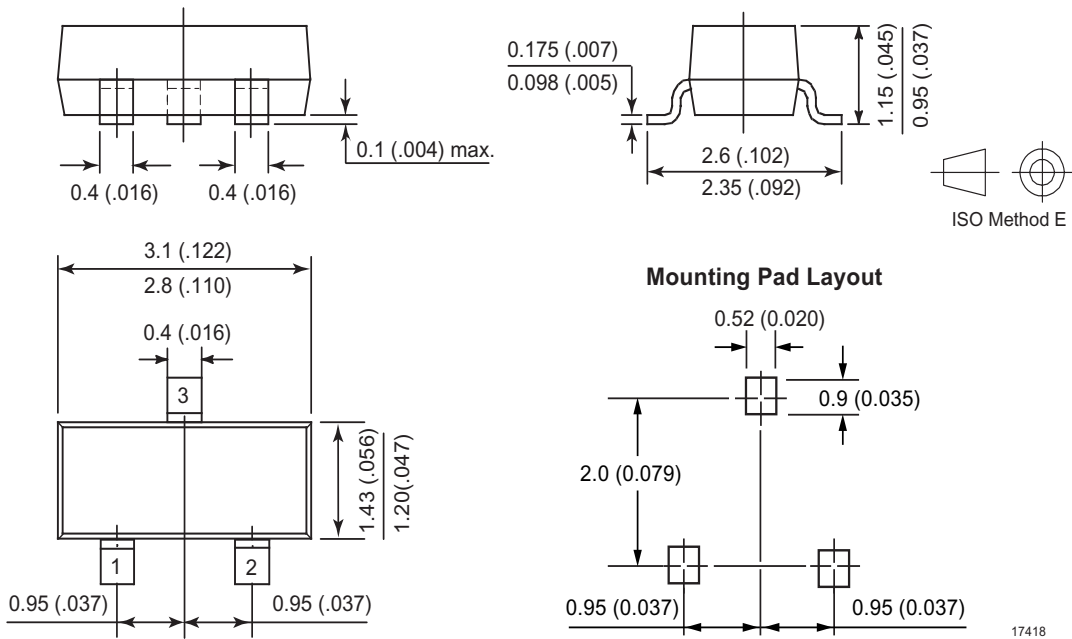


Figure 3. Typical Variation of Reverse Current at Various Temperatures

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## Package Dimensions in mm (Inches)



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